

PART ONE: General description

Resist

Process name

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Process Code

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Contact Information (Email)

07/12/00

Last Update

Etching of resist/organic material – leftovers
Can modify process “resist” already saved on the RIE system.

General description of process

PART TWO: Details

RIE Etching

Pressure Set

100

Oxygen Set

100

RF Power Set

150

CHF3 Set

0

End Point Set

900

SF6 Set

0

Process Time

15

sec

Base Pressure Set

150

PART THREE: General Comments

Use before evaporation/deposition , or etching.
The Oxygen-plasma etches some of the resist so make sure to limit the length of the process. Approx. etch rate – 0.4mic/min.